### ECEN325: Electronics Spring 2024

A Graphical Approach to BJT Amplifier Design



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### Announcements

### • HW 5 due Apr 2

### Common Emitter Amp w/ Emitter Resistor



# **Typical Design Specifications**

- Loaded voltage gain, A<sub>v</sub>
- Max output swing, v<sub>omax</sub>
  - This must be satisfied at a given linearity (total harmonic distortion)
- Input and output resistance, R<sub>in</sub> & R<sub>out</sub>
- Power Supply,  $V_{CC}$

# How to set DC Biasing Conditions?

- In order to meet all design specifications, the DC biasing conditions (I<sub>C</sub>, R<sub>C</sub>) must be set appropriately
- Can transform design specifications into functions of  $I_C \& R_C$  and graph them to find acceptable solution space

# R<sub>in</sub>, V<sub>CC</sub>, & Neg. v<sub>omax</sub> Specifications

• R<sub>in</sub> Spec

$$R_{in} = R_B \| (r_{\pi} + (\beta + 1)R_{E1}) \approx \beta R_{E1}$$
$$R_{E1} \approx \frac{R_{in}}{\beta}$$



Input resistance is primarily set by R<sub>E1</sub>

# $R_{in}$ , $V_{CC}$ , & Neg. $v_{omax}$ Specifications

 Need a minimum V<sub>CE</sub> to keep transistor in active mode with maximum negative swing

Set  $V_{CE \min} = 500 mV$ (w/ 200mV design margin)



$$V_{CC} = \frac{I_C}{\alpha} R_{E1} + V_{CE\min} + v_{o\max} + I_C R_C$$
$$V_{CE\min} = V_{CC} - I_C R_C - v_{o\max} - \frac{I_C}{\alpha} R_{E1} \ge 500 mV$$



Vcc

# $R_{in}$ , $V_{CC}$ , & Neg. $v_{omax}$ Specifications

• Can solve for I<sub>C</sub>



- Minimum negative AC Swing constraint sets an upper bound on  $\rm I_{\rm C}$ 

# Pos. v<sub>omax</sub> Specification

 Need to insure with a positive swing that the output signal doesn't clip the power supply

$$V_{CC} - I_C R_C + v_{o \max} \le V_{CC}$$

$$I_C \ge \frac{v_{o \max}}{R_C}$$

$$R_{B1} \clubsuit R_C R_C$$

- Positive AC Swing constraint sets a lower bound on  $\rm I_{\rm C}$
- Additional linearity constraint (harmonic distortion) generally sets a tighter bound

### Gain Specification



Gain constraint sets a lower bound on I<sub>C</sub>

 Need a minimum amount of bias current to insure that the AC swing doesn't distort



Model a as a system which distorts

$$i_c = av_{be} = a_1v_{be} + a_2v_{be}^2 + a_3v_{be}^3 + \dots$$
  
where  $a_1 = g_m$ ,  $a_2 = \frac{1}{2}\frac{I_{CQ}}{V_{th}^2}$ ,  $\dots$   
Here  $v_{be} = v_b - v_e \approx v_b - fi_c$   
where  $f = R_E$ 



We want to express  $i_c$  as a function of  $v_b$  because that is our input

$$i_c = bv_b = b_1v_b + b_2v_b^2 + b_3v_b^3 + \dots$$

Can show that \*

$$b_1 = \frac{g_m}{1 + g_m R_E}, \quad b_2 = \frac{1}{2} \frac{I_{CQ}}{V_{th}^2 (1 + g_m R_E)^3}, \quad \dots$$

 For single-ended amplifiers with low-distortion, HD2 will dominate the distortion terms

The second - order harmonic distortion is

$$HD2 = \frac{1}{2} \frac{b_2}{b_1^2} i_{c \max} = \frac{1}{4} \left( \frac{1}{1 + g_m R_E} \right) \left( \frac{i_{c \max}}{I_{CQ}} \right)$$

To satisfy a given HD2 specification  

$$i_{cmax} \leq 4HD2(1+g_m R_E)I_{CQ}$$

$$H_C \geq \frac{\frac{V_{omax}}{R_C}}{4HD2(1+g_m R_E)} \approx \frac{\frac{V_{omax}}{R_C}}{4HD2\left(\frac{I_C}{V_{th}}\right)R_E}$$

$$I_C \geq \frac{1}{2}\sqrt{\frac{V_{th}V_{omax}}{R_C R_E HD2}}$$
Using  $R_E \approx \frac{R_{in}}{\beta}$ 

$$I_C \geq \frac{1}{2}\sqrt{\frac{V_{th}V_{omax}\beta}{R_C R_E HD2}}$$

- HD2 will dominate, but is not the only distortion term
- For a -30dB THD, perhaps set HD2 to -40dB or (0.01)

### **Output Resistance Specification**

 Neglecting transistor output resistance, R<sub>out</sub> is determined by RC



$$R_C \leq R_{out,spec}$$

### Key CE Amp Design Equation Summary

Neg. Swing, Rin, 
$$V_{CC}$$
:  $I_C \leq \frac{V_{CC} - v_{omax} - 0.5V}{R_C + \frac{R_{in}}{\alpha\beta}}$   
Pos. Swing:  $I_C \geq \frac{v_{omax}}{R_C}$   
Gain:  $I_C \geq \frac{|A_v|V_{th}}{R_C \|R_L - \frac{|A_v|R_{in}}{\alpha\beta}}$   
Harmonic Distortion:  $I_C \geq \frac{1}{2}\sqrt{\frac{V_{th}v_{omax}\beta}{R_C R_{in}HD2}}$   
Output Resistance:  $R_C \leq R_{out,spec}$ 

## **Design Example - Specifications**

- $|A_v| \ge |-8|$
- $R_L = 200 k\Omega$
- $R_{in} \geq 200 k\Omega$
- $R_{out} \leq 30 k\Omega$
- $V_{omax} = 20mV_{pk}$  w/ THD  $\leq -30dB$
- $V_{CC} = 5V$

## **Design Equation Plots**



- Pick a design point in the middle for margin
- $I_C = 78 \mu A$ ,  $R_C = 24 k\Omega$

# **DC Operating Points**



 DC bias points must be reasonable for the circuit to work as designed!

## AC Gain, Rin, & Rout



### • $|A_v| = 19.2 dB = 9.12$

### • $R_{in} = 106.6 dB\Omega = 214 k\Omega$

### • $R_{out} = 87.7 dB\Omega = 24.0 k\Omega$

### **Transient & Distortion**

### • Output with swing $> v_{omax}$



### FFT of output signal



HARMONIC FREQUENCY FOURIER NORMALIZED PHASE NORMALIZED NO (HZ) COMPONENT <u>COMPONENT</u> (DEG) PHASE (DEG)

 1
 1.000E+04
 2.273E-02
 1.000E+00
 1.795E+02
 0.000E+00

 2
 2.000E+04
 1.462E-05
 6.433E-04
 2.901E+01
 -3.301E+02

 3
 3.000E+04
 1.164E-05
 5.121E-04
 1.7]18E+02
 -3.669E+02

 4
 4.000E+04
 1.168E-05
 5.139E-04
 2.415E+01
 -6.940E+02

 5
 5.000E+04
 1.084E-05
 4.771E-04
 -1.235E+02
 -1.021E+03

TOTAL HARMONIC DISTORTION = 1.080592E-01 PERCENT This is equal to a THD of -59.3dB.

## Fourier/THD Simulation in Multisim

#### 1.8 Total Harmonic Distortion (Fourier Simulation)

• Click on "Select Active Analysis" in Fig. 3, then click on "Fourier" (Fig. 7)

Figure 7: Fourier simulation setup

- Calculate T = 1/f<sub>i</sub>, where f<sub>i</sub> is the input frequency, and set N = 9
- On the "Analysis Parameters" tab, select:
  - Frequency resolution (fundamental frequency): f<sub>i</sub>
  - Number of harmonics: N
  - Stop time for sampling (TSTOP): 107
- Click on "Edit transient analysis", select:
  - Start time (TSTART): 0
  - End time (TSTOP): 107
  - Check "Maximum time step (TMAX)" and enter the value:  $\frac{T}{100(N+1)}$
- On the "Output" tab, click on "V(Vo)", then "Add", then "Save"
- Click on "Run" in Fig. 3
- <u>https://people.engr.tamu.edu/spalermo/ecen325/MultiSim-AnalogDiscovery2-Keysight-Manual.pdf</u>
- See page 5

# Adding $R_{E2}$ to Stabilize DC Biasing

- Adding RE2 can help to make the DC biasing less sensitive to the absolute transistor Beta value
  - Assume I want  $I_c \sim 80 \mu A$
  - While the nominal  $\beta$  is 110, assume that it can vary from 70-200
  - What is the difference in designs with  $R_{E2}=0$  and with 1V across  $R_{E2}$ ?  $\beta \sim 70$   $\beta \sim 110$   $\beta \sim 200$



| Beta | I <sub>c</sub> (No R <sub>E2</sub> ) | % Diff. from β=110 | $I_{C}$ (w/ 1V $R_{E2}$ ) | % Diff. from β=110 |
|------|--------------------------------------|--------------------|---------------------------|--------------------|
| 70   | 53µA                                 | -32.1%             | 69µA                      | -12.7%             |
| 110  | 78µA                                 | N/A                | 79µA                      | N/A                |
| 200  | 116µA                                | 48.7%              | 88µA                      | 11.4%              |

• What is the impact on the graphical design procedure?

# $R_{in}, V_{CC}, \&$ Neg. $v_{omax}$ Specs w/ $R_{E2}$

- The only equation impacted is the Neg. v<sub>omax</sub>
- Need a minimum V<sub>CE</sub> to keep transistor in active mode with maximum negative swing <sup>¬</sup><sub>B■</sub>

Set  $V_{CE \min} = 500 mV$ (w/ 200mV design margin)

$$V_{CC} = \frac{I_C}{\alpha} (R_{E1} + R_{E2}) + V_{CE\min} + v_{o\max} + I_C R_C$$

$$V_{CE\min} = V_{CC} - I_C R_C - v_{o\max} - \frac{I_C}{\alpha} R_{E1} - I_E R_{E2} \ge 500 mV$$

Vcc

 $R_{B2}$ 

R<sub>c</sub>:

 $R_{E1} \ge$ 

R<sub>E2</sub>

# $R_{in}, V_{CC}, \&$ Neg. $v_{omax}$ Specs w/ $R_{E2}$

• Can solve for  $I_C$ , assuming a  $V_{RE2}$  across  $R_{E2}$ 



• Minimum negative AC Swing constraint sets an upper bound on  $I_C$  which is reduced with  $R_{E2}$ 

### Key CE Amp Design w/ R<sub>E2</sub> Eq. Summary

Neg. Swing, Rin, V<sub>CC</sub>: 
$$I_C \leq \frac{V_{CC} - v_{omax} - 0.5V - V_{R_{E2}}}{R_C + \frac{R_{in}}{\alpha\beta}}$$
  
Pos. Swing:  $I_C \geq \frac{v_{omax}}{R_C}$   
Gain:  $I_C \geq \frac{|A_v|V_{th}}{R_C ||R_L - \frac{|A_v|R_{in}}{\alpha\beta}}$   
Harmonic Distortion:  $I_C \geq \frac{1}{2}\sqrt{\frac{V_{th}v_{omax}\beta}{R_CR_{in}HD2}}$   
Output Resistance:  $R_C \leq R_{out,spec}$ 

### **Common Collector Amp**



# **Typical Design Specifications**

- Loaded voltage gain, A<sub>v</sub>
- Max output swing, v<sub>omax</sub>
  - This must be satisfied at a given linearity (total harmonic distortion)
- Input and output resistance, R<sub>in</sub> & R<sub>out</sub>
  - If you know  $R_L$ , then  $R_{out}$  spec is somewhat redundant with  $A_v$  spec
- Power Supply,  $V_{CC}$

# How to set DC Biasing Conditions?

- In order to meet all design specifications, the DC biasing conditions (I<sub>E</sub>, R<sub>E</sub>) must be set appropriately
- Can transform design specifications into functions of  $I_E \& R_E$  and graph them to find acceptable solution space

# **R**<sub>in</sub> Specification

R<sub>in</sub> Spec

$$R_{in} = R_B \left\| \left( r_{\pi} + \left( \beta + 1 \right) \left( R_E \| R_L \right) \right) \approx \beta \left( R_E \| R_L \right) \right\|$$





 Input resistance is primarily set by R<sub>E</sub> and somewhat independent of I<sub>E</sub>

# Neg. v<sub>omax</sub> Specification

 Need to insure with a negative swing that the output signal doesn't clip the power supply



- Negative AC Swing constraint sets a lower bound on  $\mathrm{I}_\mathrm{E}$
- Additional linearity constraint (harmonic distortion) generally sets a tighter bound

# Pos. v<sub>omax</sub> & V<sub>CC</sub> Specifications

 Need a minimum V<sub>CE</sub> to keep transistor in active mode with maximum positive swing

Set  $V_{CE \min} = 500 mV$ (w/ 200mV design margin)

- V<sub>CC</sub> Spec (w/ max positive swing)
- Maximum positive AC swing constraint sets an upper bound on  $\rm I_{\rm E}$



$$V_{CC} = I_E R_E + v_{o\max} + V_{CE\min}$$
$$V_{CE\min} = V_{CC} - I_E R_E - v_{o\max} \ge 500 mV$$

$$I_E \leq \frac{V_{CC} - v_{o\max} - 0.5V}{R_E}$$

### Gain Specification





### • Gain constraint sets a lower bound on $I_E$

• Following a similar procedure as the Common-Emitter Amp, can relate the HD2 specification to the ratio of AC current  $i_c$  to  $I_{CQ}$ 

 $i_c \leq 4(HD2)(1 + g_m(R_E || R_L))I_{CO}$ 

Now, assuming a high 
$$\beta$$
 or  $\alpha \approx 1$   
 $i_e \leq 4(HD2)(1 + g_m(R_E ||R_L))I_{EQ}$   
 $I_{EQ} \geq \frac{\frac{v_{omax}}{R_E ||R_L}}{4(HD2)(1 + g_m(R_E ||R_L))} \approx \frac{\frac{v_{omax}}{R_E ||R_L}}{4(HD2)\left(\frac{I_{EQ}}{V_{th}}\right)(R_E ||R_L)}$   
 $I_{EQ} \geq \frac{1}{2(R_E ||R_L)}\sqrt{\frac{V_{th}v_{omax}}{HD2}}$ 

- HD2 will dominate the distortion terms
- For a -30dB THD, perhaps set HD2 to -40dB or (0.01)

### Key CC Amp Design Equation Summary

$$\begin{aligned} \operatorname{Rin}: \ R_E \geq & \left(\frac{\beta}{R_{in,spec}} - \frac{1}{R_L}\right)^{-1} \\ \operatorname{Neg.vomax}: \ I_E \geq & \frac{v_{o\max}}{R_E} \\ \operatorname{Pos vomax}, \operatorname{Vcc}: \ I_E \leq & \frac{V_{CC} - v_{o\max} - 0.5V}{R_E} \\ \operatorname{Gain}: \ I_E \geq & \frac{A_v V_{th}}{(R_E \| R_L)(1 - A_v)} \\ \end{aligned}$$
Harmonic Distortion: 
$$I_E \geq & \frac{1}{2(R_E \| R_L)} \sqrt{\frac{V_{th} v_{o\max}}{HD2}} \end{aligned}$$

## **Design Example - Specifications**

- $A_v \ge 0.95$
- $R_{in} \ge 1 k \Omega$
- $V_{omax} = 500 \text{mV}_{pk} \text{ w/ THD} \le -30 \text{dB}$ • Here I set HD2=40dB or 0.01
- $V_{CC} = 5V$
- $R_L = 50\Omega$

## **Design Equation Plots**



- Pick a low I<sub>E</sub> design point to save power
- $I_E = 20$ mA,  $R_E = 100\Omega$

# **DC Operating Points**



 DC bias points must be reasonable for the circuit to work as designed!

### AC Gain & Rin



### • $|A_v| = -0.38$ dB = 0.96

### • $R_{in} = 67.6 dB\Omega = 2.4 k\Omega$

### **Transient & Distortion**

### • Output with swing $> v_{omax}$



HARMONIC FREQUENCY FOURIER NORMALIZED PHASE NORMALIZED NO (HZ) COMPONENT COMPONENT (DEG) PHASE (DEG)

- 1 1.000E+04 5.032E-01 1.000E+00 1.770E+00 0.000E+00
- 2 2.000E+04 5.146E-03 1.023E-02 -8.968E+01 -9.322E+01
- 3 3.000E+04 1.798E-03 3.572E-03 2.109E+00 -3.200E+00
- 4 4.000E+04 4.937E-04 9.811E-04 1.251E+02 1.180E+02
- 5 5.000E+04 1.410E-04 2.801E-04 8.911E+01 8.027E+01

TOTAL HARMONIC DISTORTION = 1.088050E+00 PERCENT